Ordering number:2041A

PNP/NPN Epitaxial Planar Silicon Transistors



# 2SB1144/2SD1684

# 100V/1.5A Switching Applications

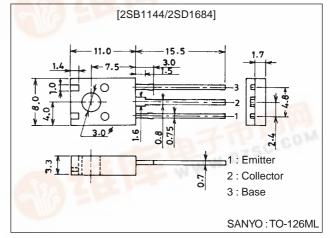
#### **Features**

- · Adoption of FBET and MBIT processes.
- · High breakdown voltage.
- · Low saturation voltage.
- Plastic-covered heat sink facilitating high-density mounting.

### **Package Dimensions**

unit:mm

2042B



(): 2SB1144

## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)120	V
Collector-to-Emitter Voltage	VCEO		(-)100	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(–)6	V
Collector Current	I <sub>C</sub>		(–)1.5	Α
Collector Current (Pulse)	I <sub>CP</sub>	- mile (1)	(–)2.0	Α
Collector Dissipation	PC	A STATE OF THE STA	1.5	W
		Tc=25°C	10	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	D Table	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Cumbal	Conditions		Unit		
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)100V, I <sub>E</sub> =0			(-)100	nA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0		-	(-)100	nA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)100mA	100*		400*	,07
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A	30	M 10 3	200	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)50mA	41.41	(100)		MHz
				120		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		11(18)		pF

<sup>\*:</sup> The 2SB1144/2SD1684 are classified by 100mA hee as follows:

ш	100	Q	200	140	S	280	200	Т	400

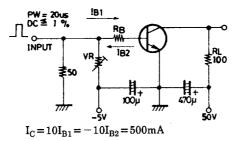
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- SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges,or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters

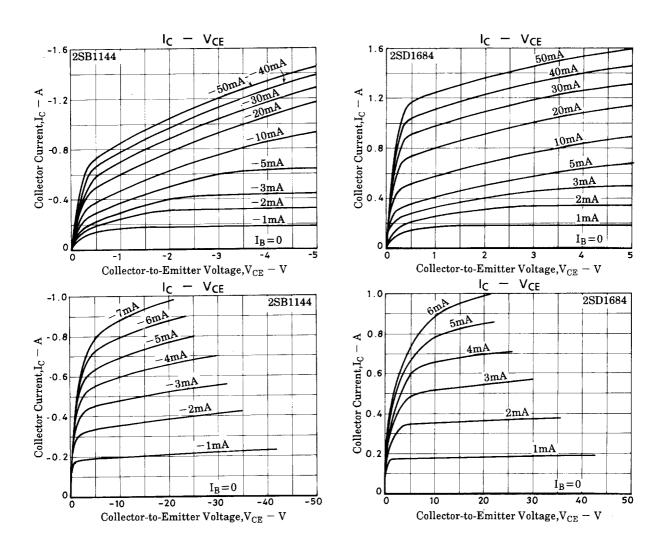
### 2SB1144/2SD1684

Parameter	Cumphal	Conditions		Ratings			
Parameter	Symbol	Conditions		typ	max	Unit	
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA		(-180)	(-500)	mV	
				100	300	mV	
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)500mA, I <sub>B</sub> =(-)50mA		(–)0.85	(–)1.2	V	
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10μΑ, I <sub>E</sub> =0	(-)120			V	
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(-)100			V	
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(-)10μΑ, I <sub>C</sub> =0	(-)6			V	
Turn-ON Time	ton	See specified Test Circuit		(80)80		ns	
Storage Time	t <sub>stg</sub>	See specified Test Circuit		1000		ns	
				(750)		ns	
Fall Time	t <sub>f</sub>	See specified Test Circuit		(40)50		ns	

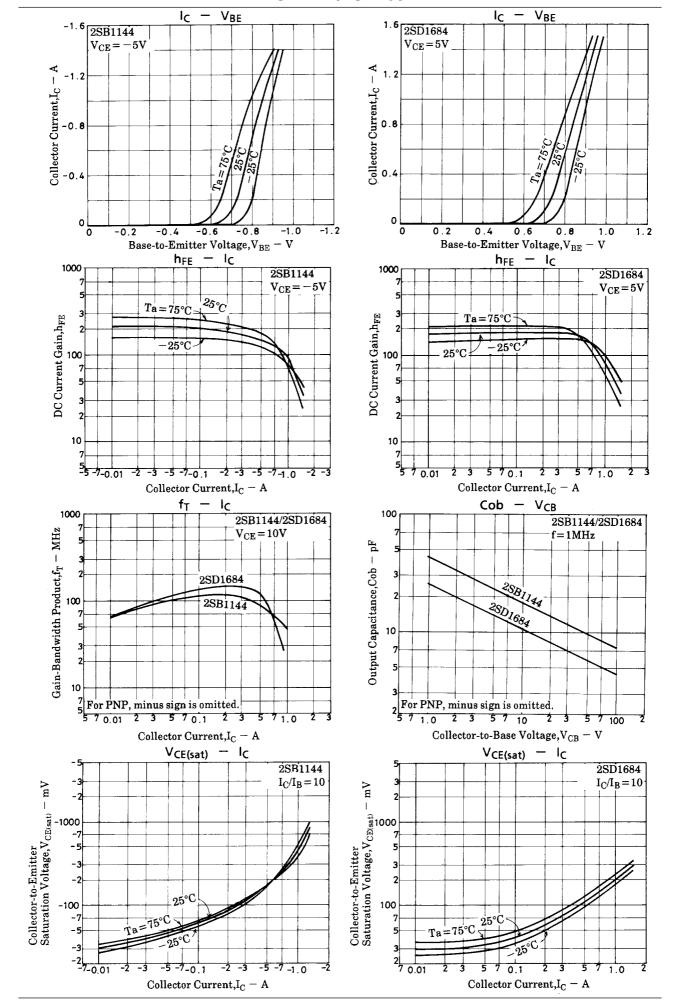
### **Switching Time Test Circuit**



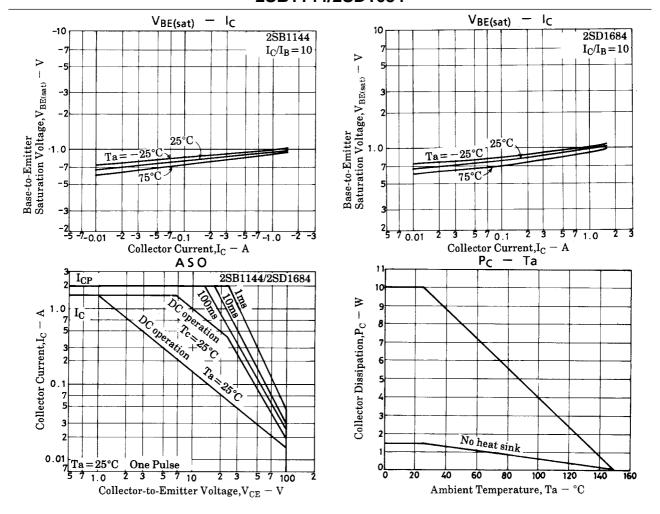
Unit (resistance:  $\Omega$ , capacitance: F))



### 2SB1144/2SD1684



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